# Efficient Charge Separation and Visible-Light Response of Two-

## Dimensional Janus Group-III Monochalcogenide multilayers

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Fig. S1 Phonon dispersion curves (left panels) and variation of total energy against the time in AIMD simulations (right panels) for Janus  $M_2XY$  monolayers. The temperature is set to 300 K. The insets show snapshots of atomic structures at the end of AIMD simulations.



Fig. S2 The band structures (Left panels) and partial charge density of CB and VB (right panels) of Janus  $M_2XY$  monolayers according to the HSE06 functional. Fermi level is indicated by a dashed line. The VBM and CBM are shown with red points. The isosurface value is 0.003 e/bohr<sup>3</sup>.

#### The different stacking and stability for Janus multilayer

Here, we consider three different stacking configurations in the vertical direction with five possible high-symmetry stacking orders in the in-plane direction for each stacking configuration. The stability of the multilayer can be evaluated by binding energy  $E_{\rm b}$  according to the following equation:

$$E_{\rm b} = (E_n - nE_{\rm monolayer})/S$$

where  $E_n$  is the total energy of Janus M<sub>2</sub>XY multilayer (*n* is the number of the layers) with a different stacking pattern and  $E_{\text{monolayer}}$  is the total energy of isolated Janus M<sub>2</sub>XY monolayer, while *S* is the transverse area of multilayer. The calculated binding energy ( $E_b$ ), and ground-state stacking order for bilayer are listed in Table S1. The disparity in the magnitude of their corresponding binding energy and ground-state stacking order for different stacking pattern are found. The negative binding energies indicate that Janus M<sub>2</sub>XY bilayers are energetically favorable and can be easily formed by an exothermic reaction. However, the ground-state stacking order is different for Janus M<sub>2</sub>XY bilayer with different system, except the X-Y-X-Y stacking configurations, whose ground-state structure are all H4 stacking order, as listed in Table S1. As for trilayer, quadlayer and pentalayer, the geometry structure and calculated binding energy ( $E_b$ ) are shown in Fig. S3. It is obviously that the multilayer structure becomes more and more energetic stability with increasing the number of layer.

bilayer	X-Y-X-Y		Y-X-X-Y		X-Y	X-Y-Y-X	
system	$E_{b}$	stacking	Eb	stacking	Eb	stacking	
Ga <sub>2</sub> SSe	-19.67	H4	-18.79	H4	-20.81	H2	
Ga <sub>2</sub> STe	-20.56	H4	-18.56	H4	-24.26	Н3	
Ga <sub>2</sub> SeTe	-21.09	H4	-20.03	H4	-22.83	Н3	
In <sub>2</sub> SSe	-20.17	H4	-19.56	H2	-20.94	H4	
In <sub>2</sub> STe	-21.18	H4	-20.19	Н3	-23.45	Н3	
In <sub>2</sub> SeTe	-21.48	H4	-20.88	H4	-22.15	H2	

Table S1. The calculated binding energy  $E_b$  (meV/Å<sup>2</sup>) and the ground-state stacking order for each bilayer system.

Table S2. The calculated interlayer distance d (Å) for Janus M<sub>2</sub>XY multilayer.  $d_1$ ,  $d_2$ ,  $d_3$ , and  $d_4$  are labeled in Fig. S7(a).

multilayer		Ga <sub>2</sub> SSe	Ga <sub>2</sub> STe	Ga <sub>2</sub> SeTe	In <sub>2</sub> SSe	In <sub>2</sub> STe	In <sub>2</sub> SeTe
trilayer	$d_1$	3.063	3.145	3.165	2.860	2.920	2.938
	$d_2$	3.073	3.113	3.127	2.825	2.879	2.900
quadlayer	$d_1$	3.098	3.138	3.158	2.847	2.899	2.912
	$d_2$	3.070	3,128	3.146	2.862	2.905	2.920
	$d_3$	3.071	3.139	3.158	2.849	2.890	2.910
pentalayer	$d_1$	3.103	3.131	3.148	2.837	2.895	2.914
	$d_2$	3.079	3.119	3.134	2.848	2.902	2.917
	$d_3$	3.059	3.123	3.137	2.853	2.903	2.920
	$d_4$	3.062	3.131	3.148	2.837	2.890	2.910



Fig. S3 (a) Side views and (b) the binding energies of Janus  $M_2XY$  multilayer. The interlayer distance *d* is marked in the figure and the values are listed in Table S2.

Due to the larger time consuming, only the bilayers of phonon dispersion curves in X-Y-X-Y stacking configuration are calculated with  $4 \times 4 \times 1$  supercell and  $3 \times 3 \times 1 k$ points, as shown in Fig. S4. All the phonon modes of bilayer structures are similar to the case of monolayers and are all positive, indicating that they are dynamical stability. At the same time, we perform the ab initial dynamics simulation at 300 K with the simulation time lasts for 6 ps for all the multilayer structures. The snapshots of atomic structures at the time of 6 ps are shown in Fig. S5. It is clearly seen that there are not significant distortions for them, confirming their thermal stability.



Fig. S4 Phonon dispersion curves for Janus M<sub>2</sub>XY bilayers, respectively.



Fig. S5 The snapshot of atomic structures for Janus multilayers after first-principles molecular dynamics simulation, respectively.



Fig. S6 The partial charge density of CB and VB of Janus  $M_2XY$  bilayers in X-Y-X-Y stacking configuration according to the HSE06 functional. The isosurface value is 0.003 e/bohr<sup>3</sup>.



Fig. S7 The band structures (Left panels) and partial charge density of CB and VB (right panels) of Janus  $M_2XY$  bilayers in X-Y-Y-X stacking configuration according to the HSE06 functional. The Fermi level is indicated by a dashed line. The VBM and CBM are shown with red points. The isosurface value is 0.003 e/bohr<sup>3</sup>.



Fig. S8 Planar average electrostatic potential energy of the Janus  $M_2XY$  bilayer in X-Y-Y-X stacking configuration.



Fig. S9 Band alignments of Janus  $M_2XY$  monolayers where the vacuum level is set to 0 eV. E denotes the internal electric field.



Fig. S10 The partial charge density of conduction band (Top) and valence band (Bottom) for Janus M<sub>2</sub>XY multilayer in X-Y-X-Y stacking configuration. The isosurface value is 0.003 e/ bohr<sup>3</sup>.

#### Free energy difference ( $\Delta G$ )

Free energy difference ( $\Delta G$ ) for water redox reactions is evaluated based on the spin-polarized calculation, according to the following equation

$$\Delta G = \Delta E + \Delta ZPE - T\Delta S + \Delta G_{pH} + \Delta G_{U}$$

where  $\Delta E$  is the absorption energy of the intermediates.  $\Delta ZPE$  and  $\Delta S$  are the differences of zero point energy and entropy between the adsorbed intermediates and the gas phase. *T* is the temperature (298.15K in our work).  $\Delta G_{pH}$  and  $\Delta G_U$  are the free energy correction, which depends on the pH value and applied electrode potential *U*, respectively. They can be calculated by:

$$\Delta G_{pH} = -k_B T \ln(10) \cdot pH \approx -0.059 eV \cdot pH$$
$$\Delta G_{U} = -eU$$

#### Hydrogen Evolution Reaction (HER)

HER mechanism involves two-electron pathways, satisfying the following two elementary steps:

$$* +H^{+} + e^{-} \rightarrow *H$$
$$*H +H^{+} + e^{-} \rightarrow H_{2} + *$$

### **Oxygen Evolution Reaction (OER)**

OER mechanism involves four-electron oxidation pathways, which can be demonstrated by

$$*+H_{2}O \rightarrow *OH+H^{+} + e^{-}$$
$$*OH \rightarrow *O + H^{+} + e^{-}$$
$$*O+H_{2}O \rightarrow *OOH+H^{+} + e^{-}$$
$$*OOH \rightarrow *+O_{2} + H^{+} + e^{-}$$

where \* represents the active site, \*OH, \*O, \*OOH and \*H represent the adsorbed intermediates.